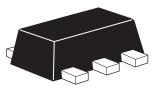
# ZXTN5551Z 160V, SOT89, NPN high voltage transistor

### Summary

 $BV_{CEO} > 160V$   $BV_{EBO} > 6V$   $I_{C(cont)} = 600mA$   $P_D = 1.2W$ Complementary part number ZXTP5401Z



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SEMICONDUCTORS

### Description

A high voltage NPN transistor in a small outline surface mount package

### Features

- 160V rating
- SOT89 package

### Applications

• High voltage amplification

### Ordering information

Device	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
ZXTN5551ZTA	7	12	1000

# c C C C B Pinout - top view

### **Device marking**

N51

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# **ZXTN5551Z**

### Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	180	V
Collector-emitter voltage	V <sub>CEO</sub>	160	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Continuous collector current <sup>(a)</sup>	Ι <sub>C</sub>	600	mA
Power dissipation at $T_A = 25^{\circ}C^{(a)}$	P <sub>D</sub>	1.2	W
Linear derating factor		9.6	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

### Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient <sup>(a)</sup>	$R_{\ThetaJA}$	104	°C/W

### NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

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Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	180	270		V	I <sub>C</sub> = 100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	160	200		V	I <sub>C</sub> = 1mA <sup>(*)</sup>
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	7.85		V	I <sub>E</sub> = 10μA
Collector cut-off current	I <sub>CBO</sub>		<1	50	nA	V <sub>CB</sub> = 120V
				50	μA	$V_{CB} = 120V, T_{amb} = 100^{\circ}C$
Collector-emitter	V <sub>CE(sat)</sub>		65	150	mV	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 1 {\rm mA}^{(*)}$
saturation voltage			115	200	mV	$I_{C} = 50 \text{mA}, I_{B} = 5 \text{mA}^{(*)}$
Base-emitter saturation	$V_{BE(sat)}$		760	1000	mV	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 1 {\rm mA}^{(*)}$
voltage			840	1200	mV	$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 5 {\rm mA}^{(*)}$
Static forward current	h <sub>FE</sub>	80	130			I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V <sup>(*)</sup>
transfer ratio		80	145	250		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V <sup>(*)</sup>
		30	65			$I_{C} = 50 \text{mA}, V_{CE} = 5 V^{(*)}$
Transition frequency	f <sub>T</sub>		130		MHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V f = 100MHz
Output capacitance	C <sub>OBO</sub>			6	pF	V <sub>CB</sub> = 10V, f = 1MHz <sup>(*)</sup>
Small signal	h <sub>FE</sub>	50		260		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V, f=1kHz <sup>(†)</sup>
Delay time	t <sub>(d)</sub>		95		ns	V <sub>CC</sub> = 10V. I <sub>C</sub> = 10mA,
Rise time	t <sub>(r)</sub>		64		ns	I <sub>B1</sub> = I <sub>B2</sub> = 1mA.
Storage time	t <sub>(s)</sub>		1256		ns	
Fall time	t <sub>(f)</sub>		140		ns	

# Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

### NOTES:

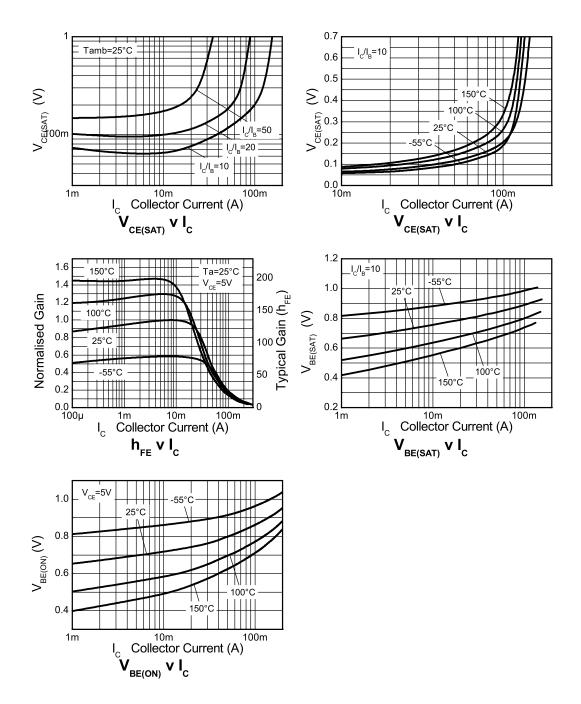
(\*) Measured under pulsed conditions. Pulse width  $\leq$ 300 $\mu$ s; duty cycle  $\leq$ 2%.

(†) Periodic sample test only

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### **Typical characteristics**



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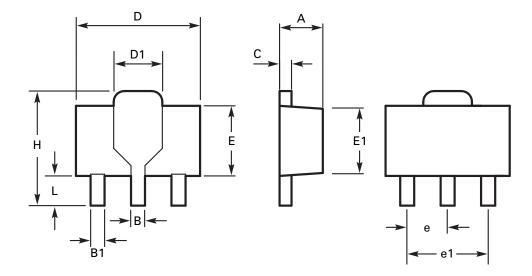
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# **ZXTN5551Z**

### Package outline - SOT89



DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
В	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	е	1.50 BSC		0.059 BSC	
С	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118	BSC
D	4.40	4.60	0.173	0.181	Н	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

# **ZXTN5551Z**

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